TD-SCDMA 2010 MHz to 2025 MHz fully integrated Doherty transistor

AMPLEON

Rev. 3 — 1 September 2015

Product data sheet

1. Product profile

1.1 General description

The BLD6G21L-50 and BLD6G21LS-50 incorporate a fully integrated Doherty solution using Ampleon's state of the art GEN6 LDMOS technology. This device is perfectly suited for TD-SCDMA base station applications at frequencies from 2010 MHz to 2025 MHz. The main and peak device, input splitter and output combiner are integrated in a single package. This package consists of one gate and drain lead and two extra leads of which one is used for biasing the peak amplifier and the other is not connected. It only requires the proper input/output match and bias setting as with a normal class-AB transistor.

Table 1. Typical performance

RF performance at $T_h = 25$ °C.

Mode of operation	f	V _{DS}	P _{L(AV)}	Gp	η_{D}	ACPR	P _{L(3dB)}
	(MHz)	(V)	(W)	(dB)	(%)	(dBc)	(W)
TD-SCDMA [1][2]	2010 to 2025	28	8	14.5	43	-24	53

^[1] Test signal: 6-carrier TD-SCDMA; PAR = 10.8 dB at 0.01 % probability on CCDF.

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Therefore care should be taken during transport and handling.

1.2 Features and benefits

- Typical TD-SCDMA performance at frequencies from 2010 MHz to 2025 MHz:
 - ◆ Average output power = 8 W
 - Power gain = 14.5 dB
 - ◆ Efficiency = 43 %
- Fully optimized integrated Doherty concept:
 - integrated asymmetrical power splitter at input
 - integrated power combiner
 - peak biasing down to 0 V
 - low junction temperature
 - high efficiency
- 100 % peak power tested for guaranteed output power capability

^[2] $I_{Dq} = 170 \text{ mA (main)}$; $V_{GS(amp)peak} = 0 \text{ V}$.

TD-SCDMA 2010 MHz to 2025 MHz fully integrated Doherty transistor

- Integrated ESD protection
- Good pair match (main and peak on the same chip)
- Independent control of main and peak bias
- Internally matched for ease of use
- Excellent ruggedness
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

1.3 Applications

High efficiency RF power amplifiers with digital pre-distortion for TD-SCDMA multi carrier applications in the 2010 MHz to 2025 MHz range.

2. Pinning information

Table 2. Pinning

Pin	Description		Simplified outline	Graphic symbol
BLD6G21	L-50 (SOT1130A)			
1	drain			
2	gate + bias main		1	1
3	source	<u>[1]</u>		2
4	n.c.		3	2 3
5	bias peak		4 2 5	001aak920
BLD6G21	LS-50 (SOT1130B)			
1	drain			
2	gate + bias main		1	1
3	source	<u>[1]</u>		2
4	n.c.		3	2 3
5	bias peak		2 5	001aak920

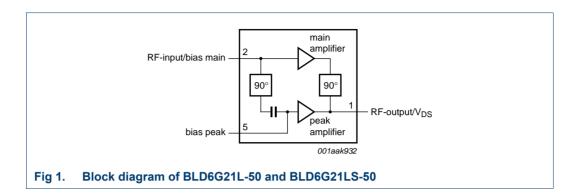
^[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Packag	Package			
	Name	Description	Version		
BLD6G21L-50	-	flanged ceramic package; 2 mounting holes; 4 leads	SOT1130A		
BLD6G21LS-50	-	earless flanged ceramic package; 4 leads	SOT1130B		

4. Block diagram



5. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Valid for both main and peak device.

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	65	V
V _{GS(amp)main}	main amplifier gate-source voltage		-0.5	+13	V
V _{GS(amp)peak}	peak amplifier gate-source voltage		-0.5	+13	V
I _D	drain current		-	10.2	Α
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	200	°C

6. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
R _{th(j-case)}	thermal resistance from junction to case	T_{case} = 80 °C; P_L = 8 W	<u>[1]</u> 2.1	K/W

^[1] When operated with a 6-carrier TD-SCDMA modulated signal with PAR = 10.8 dB at 0.01 % probability on CCDF.

7. Characteristics

Table 6. Characteristics

Valid for both main and peak device.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{(BR)DSS} \\$	drain-source breakdown voltage	V_{GS} = 0 V; I_{D} = 0.62 mA	65	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	V_{DS} = 10 V; I_{D} = 31 mA	1.4	1.8	2.4	V
V_{GSq}	gate-source quiescent voltage	V_{DS} = 28 V; I_{D} = 170 mA	1.55	2.05	2.55	V
I _{DSS}	drain leakage current	$V_{GS} = 0 \text{ V}; V_{DS} = 28 \text{ V}$	-	-	1.4	μΑ
I _{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	4.95	5.5	-	Α

BLD6G21L-50_BLD6G21LS-50#3

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TD-SCDMA 2010 MHz to 2025 MHz fully integrated Doherty transistor

 Table 6.
 Characteristics ...continued

Valid for both main and peak device.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{GSS}	gate leakage current	V_{GS} = 11 V; V_{DS} = 0 V	-	-	140	nA
9 _{fs}	forward transconductance	V_{DS} = 10 V; I_{D} = 1.55 A	1.4	2.2	-	S
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 1.085 \text{ A}$	-	0.52	0.736	Ω

8. Application information

Table 7. Application information

Mode of operation: 6-carrier TD-SCDMA; PAR 10.8 dB at 0.01 % probability on CCDF; f = 2017.5 MHz; RF performance at $V_{DS} = 28$ V; $I_{Dq} = 170$ mA; $V_{GS(amp)peak} = 0$ V; $T_{case} = 25$ °C; unless otherwise specified; in a production circuit.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$P_{L(AV)}$	average output power		-	8	-	W
Gp	power gain	$P_{L(AV)} = 8 W$	13	14.5	-	dB
η_{D}	drain efficiency	$P_{L(AV)} = 8 W$	39	43	-	%
PARO	output peak-to-average ratio	$P_{L(AV)} = 8 W$	-	9.4	-	dB
RLin	input return loss	$P_{L(AV)} = 8 W$	8	23	-	dB
ACPR	adjacent channel power ratio	$P_{L(AV)} = 8 W$	-	-24	-20	dBc

Table 8. Application information

Mode of operation: Pulsed CW; δ = 10 %; t_p = 100 μ s; RF performance at V_{DS} = 28 V; I_{Dq} = 170 mA; $V_{GS(amp)peak}$ = 0 V; T_{case} = 25 °C; unless otherwise specified; in a production circuit.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
P _{L(3dB)}	output power at 3 dB gain compression		46	53	-	W

8.1 Ruggedness in Doherty operation

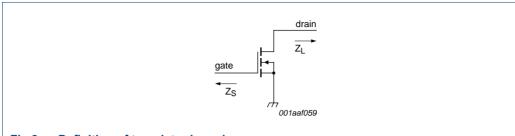
The BLD6G21L-50 and BLD6G21LS-50 are capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions: $V_{DS} = 28 \text{ V}$; $I_{Dq} = 170 \text{ mA}$; $P_L = 8 \text{ W}$ (TD-SCDMA); f = 2017.5 MHz.

8.2 Impedance information

Table 9. Typical impedance

Measured Load Pull data; typical values unless otherwise specified.

f	Z _S	Z _L
MHz	Ω	Ω
1995	3.5 – 12.3j	6.7 – 6.1j
2010	3.6 – 12.7j	6.7 – 6.1j
2017.5	3.6 – 12.7j	6.7 – 5.7j
2025	3.7 – 12.7j	6.4 – 5.2j
2040	4.0 – 12.9j	5.7 – 4.8j

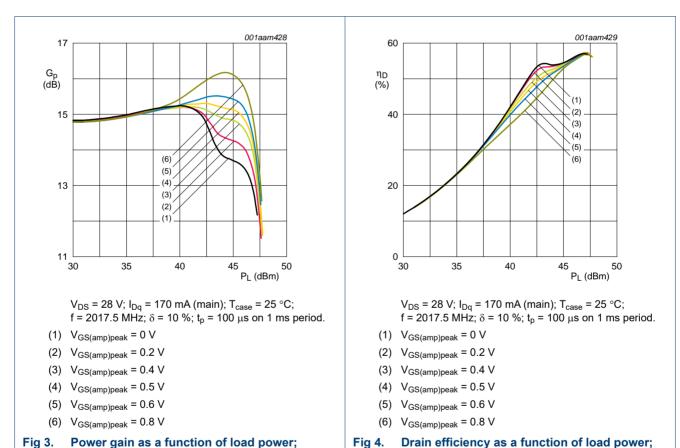


Definition of transistor impedance Fig 2.

8.3 Performance curves

Performance curves are measured in a BLD6G21L-50 application circuit.

8.3.1 CW pulsed

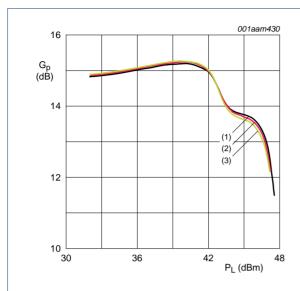


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typical values

typical values

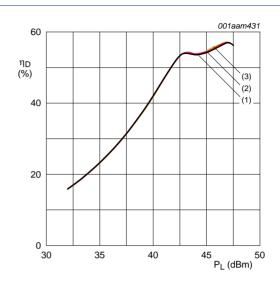
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 V_{DS} = 28 V; I_{Dq} = 170 mA (main); T_{case} = 25 °C; $V_{GS(amp)peak}$ = 0 V; δ = 10 %; t_p = 100 μs on 1 ms period.

- (1) f = 2010 MHz
- (2) f = 2018 MHz
- (3) f = 2025 MHz

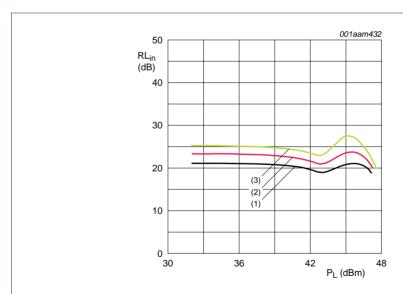
Fig 5. Power gain as a function of load power; typical values



$$\begin{split} V_{DS} = 28 \text{ V; } I_{Dq} = 170 \text{ mA (main); } T_{case} = 25 \text{ °C;} \\ V_{GS(amp)peak} = 0 \text{ V; } \delta = 10 \text{ %; } t_p = 100 \text{ } \mu\text{s on 1 ms period.} \end{split}$$

- (1) f = 2010 MHz
- (2) f = 2018 MHz
- (3) f = 2025 MHz

Fig 6. Drain efficiency as a function of load power; typical values

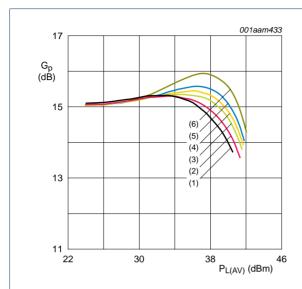


 V_{DS} = 28 V; I_{Dq} = 170 mA; $V_{GS(amp)peak}$ = 0 V; T_{case} = 25 °C; δ = 10 %; t_p = 100 μs on 1 ms period.

- (1) f = 2010 MHz
- (2) f = 2018 MHz
- (3) f = 2025 MHz

Fig 7. Input return loss as a function of load power; typical values

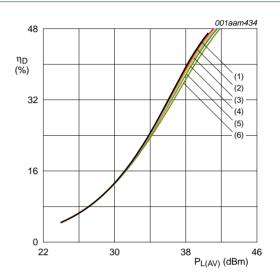
8.3.2 TD-SCDMA



 V_{DS} = 28 V; I_{Dq} = 170 mA (main); T_{case} = 25 °C; f = 2017.5 MHz; 6-carrier TD-SCDMA; PAR = 10.8 dB at 0.01 % probability on CCDF.

- (1) $V_{GS(amp)peak} = 0 V$
- (2) $V_{GS(amp)peak} = 0.2 V$
- (3) $V_{GS(amp)peak} = 0.4 V$
- (4) $V_{GS(amp)peak} = 0.5 V$
- (5) $V_{GS(amp)peak} = 0.6 V$
- (6) $V_{GS(amp)peak} = 0.8 \text{ V}$

Fig 8. Power gain as a function of average load power; typical values

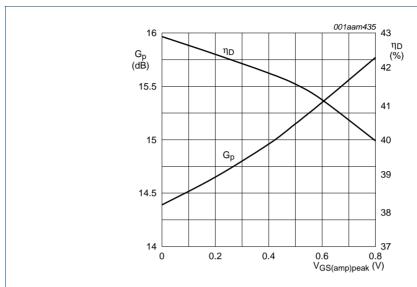


 V_{DS} = 28 V; I_{Dq} = 170 mA (main); T_{case} = 25 °C; f = 2017.5 MHz; 6-carrier TD-SCDMA; PAR = 10.8 dB at 0.01 % probability on CCDF.

- (1) $V_{GS(amp)peak} = 0 V$
- (2) $V_{GS(amp)peak} = 0.2 V$
- (3) $V_{GS(amp)peak} = 0.4 \text{ V}$
- (4) $V_{GS(amp)peak} = 0.5 V$
- (5) $V_{GS(amp)peak} = 0.6 V$
- (6) $V_{GS(amp)peak} = 0.8 \text{ V}$

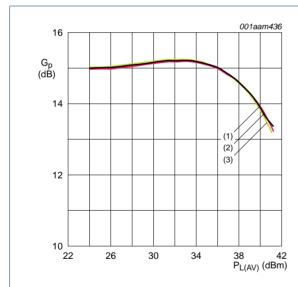
Fig 9. Drain efficiency as a function of average load power; typical values

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 V_{DS} = 28 V; I_{Dq} = 170 mA; $P_{L(AV)}$ = 8 W; T_{case} = 25 °C; f = 2017.5 MHz; 6-carrier TD-SCDMA; PAR = 10.8 dB at 0.01 % probability on CCDF.

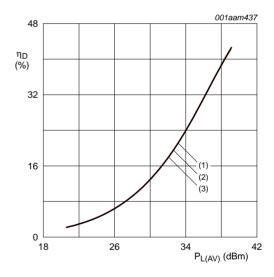
Fig 10. Power gain and drain efficiency as function of peak amplifier gate-source voltage; typical values



 V_{DS} = 28 V; I_{Dq} = 170 mA (main); T_{case} = 25 °C; $V_{GS(amp)peak}$ = 0 V; 6-carrier TD-SCDMA; PAR = 10.8 dB at 0.01 % probability on CCDF.

- (1) f = 2010 MHz
- (2) f = 2018 MHz
- (3) f = 2025 MHz

Fig 11. Power gain as a function of average load power; typical values

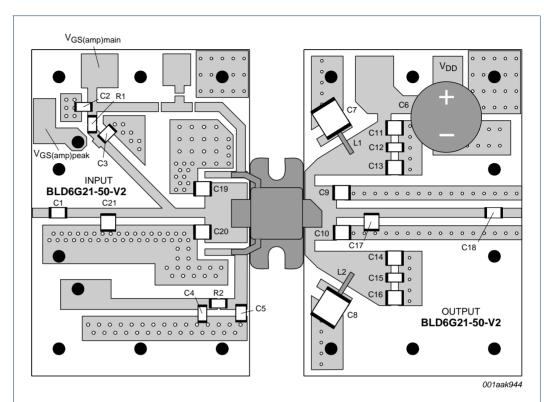


 V_{DS} = 28 V; I_{Dq} = 170 mA (main); T_{case} = 25 °C; $V_{GS(amp)peak}$ = 0 V; 6-carrier TD-SCDMA; PAR = 10.8 dB at 0.01 % probability on CCDF.

- (1) f = 2010 MHz
- (2) f = 2018 MHz
- (3) f = 2025 MHz

Fig 12. Drain efficiency as a function of average load power; typical values

9. Test information



The striplines are on a double copper-clad gold plated Rogers 4350B Printed-Circuit Board (PCB) with ϵ_r = 3.5 and thickness = 0.76 mm.

See Table 10 for list of components.

Fig 13. Component layout

Table 10. List of components
See Figure 13 for component layout.

Component	Description	Value	Dimensions
C1, C3, C5, C18	multilayer ceramic chip capacitor	9.1 pF	[1]
C2, C4, C12, C15	multilayer ceramic chip capacitor	100 nF	
C6	electrolytic capacitor	470 μF; 63 V	
C7, C8	multilayer ceramic chip capacitor	10 μF	
C9, C10	multilayer ceramic chip capacitor	1.5 pF	[1]
C11, C13, C14, C16	multilayer ceramic chip capacitor	8.2 pF	[1]
C17	multilayer ceramic chip capacitor	1.2 pF	[1]
C19, C20	multilayer ceramic chip capacitor	0.7 pF	[1]
C21	multilayer ceramic chip capacitor	1.2 pF	[1]
L1, L2	copper wire	-	diameter = 0.8 mm; length = 8 mm
R1	SMD resistor	3.6 Ω	1206
R2	SMD resistor	33 Ω	1206

^[1] American Technical Ceramics type 100B or capacitor of same quality.

BLD6G21L-50_BLD6G21LS-50#3

10. Package outline

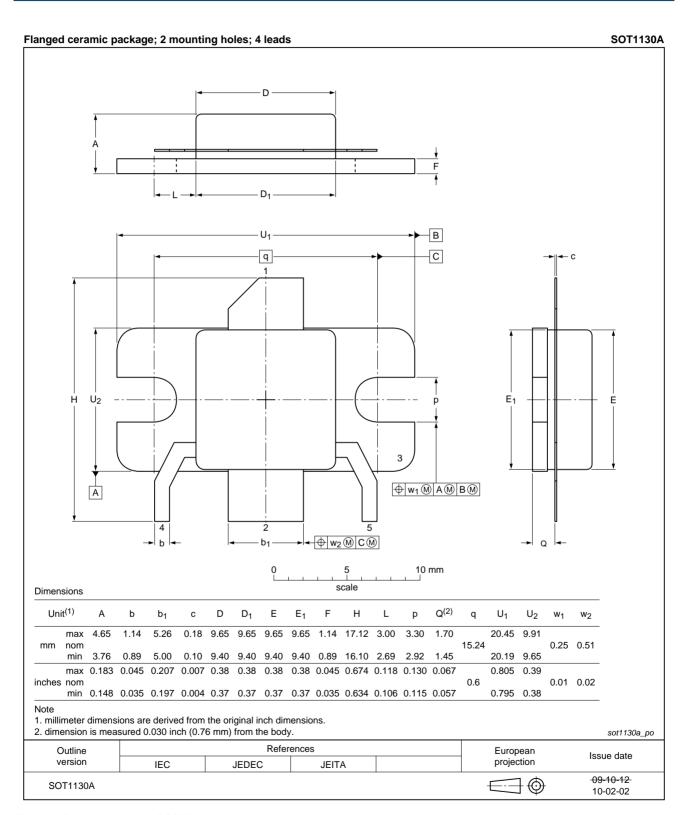


Fig 14. Package outline SOT1130A

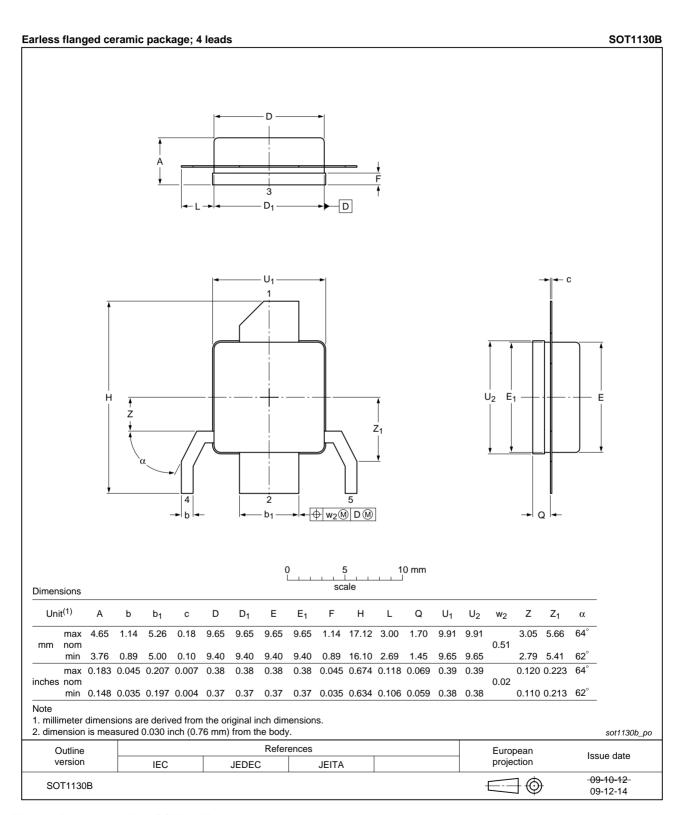


Fig 15. Package outline SOT1130B

11. Abbreviations

Table 11. Abbreviations

Acronym	Description
CCDF	Complementary Cumulative Distribution Function
CW	Continuous Wave
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
PAR	Peak-to-Average power Ratio
RF	Radio Frequency
SMD	Surface Mounted Device
TD-SCDMA	Time Division-Synchronous Code Division Multiple Access
VSWR	Voltage Standing-Wave Ratio

12. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
BLD6G21L-50_BLD6G21LS-50#3	20150901	Product data sheet	-	BLD6G21L-50_BLD6G21LS- 50 v.2	
Modifications:	 The format of this document has been redesigned to comply with the new identity guidelines of Ampleon. Legal texts have been adapted to the new company name where appropriate. 				
BLD6G21L-50_BLD6G21LS-50v.2	20100817	Product data sheet	-	BLD6G21L-50_BLD6G21LS- 50 v.1	
BLD6G21L-50_BLD6G21LS-50v.1	20091028	Objective data sheet	-	-	

TD-SCDMA 2010 MHz to 2025 MHz fully integrated Doherty transistor

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition	
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.	
Preliminary [short] data sheet Qualification This document contains data from the preliminary specification.		This document contains data from the preliminary specification.	
Product [short] data sheet	Production	This document contains the product specification.	

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- [2] The term 'short data sheet' is explained in section "Definitions"
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TD-SCDMA 2010 MHz to 2025 MHz fully integrated Doherty transistor

15. Contents

1	Product profile
1.1	General description
1.2	Features and benefits
1.3	Applications
2	Pinning information
3	Ordering information
4	Block diagram
5	Limiting values
6	Thermal characteristics
7	Characteristics
8	Application information
8.1	Ruggedness in Doherty operation
8.2	Impedance information
8.3	Performance curves
8.3.1	CW pulsed
8.3.2	TD-SCDMA
9	Test information
10	Package outline
11	Abbreviations
12	Revision history
13	Legal information1
13.1	Data sheet status
13.2	Definitions
13.3	Disclaimers
13.4	Trademarks14
14	Contact information
15	Contents 1

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